

KS54AHCT
KS74AHCT

573

Octal D-Type Transparent Latches
with 3-State Outputs

T-46-07-05

FEATURES

- 8 latches in a single package
- Full parallel access for loading
- Function, pin-out, speed and drive compability with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ($I_{OL} = 24 \text{ mA}$ @ $V_{OL} = 0.5\text{V}$) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74AHCT: -40°C to $+85^{\circ}\text{C}$
KS54AHCT: -40°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

DESCRIPTION

The '573 consists of 8 high-speed D-type latches coupled to 3-state output buffers with high drive capability. It can be used in implementing buffer registers, I/O ports, bidirectional bus drivers and working registers.

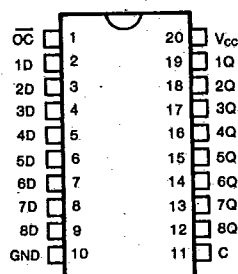
The latches are transparent: when the enable (C) is high, the Q outputs follow the data (D) inputs. When the enable is low, the outputs latch at the levels that were set up at the D inputs.

The output buffers are controlled by a common signal (OC) which places the outputs at a high-impedance state when it is taken high. The $\overline{\text{OC}}$ signal does not affect the internal operations of the latches. Old data can be retained or new data can be entered while outputs are off.

These devices provide speeds and drive capability equivalent of their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

PIN CONFIGURATION

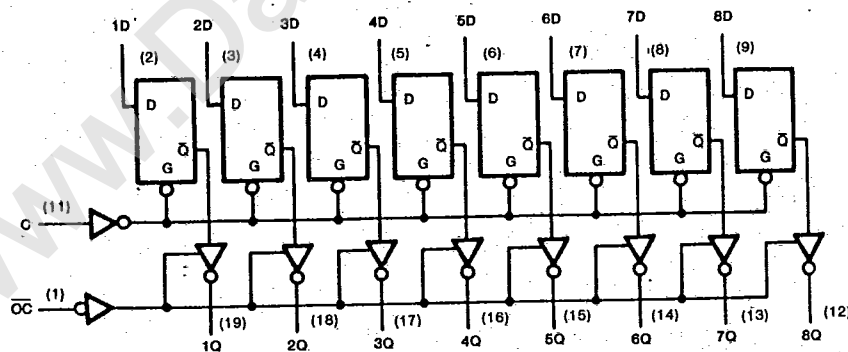


FUNCTION TABLE

(Each Latch)

Inputs			Output
$\overline{\text{OC}}$	Enable C	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

LOGIC DIAGRAM



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Absolute Maximum Ratings*

Supply Voltage Range V_{CC} -0.5V to +7V
 DC Input Diode Current, I_{IK}
 ($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
 DC Output Diode Current, I_{OK}
 ($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
 Continuous Output Current Per Pin, I_O
 ($-0.5V < V_O < V_{CC} + 0.5V$) ± 70 mA
 Continuous Current Through
 V_{CC} or GND pins ± 250 mA
 Storage Temperature Range, T_{stg} -65°C to +150°C
 Power Dissipation Per Package, P_d † 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:
 Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN} , V_{OUT} ... 0V to V_{CC}
 Operating Temperature
 Range KS74AHCT: -40°C to +85°C
 KS54AHCT: -55°C to +125°C
 Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T _a = 25°C		KS74AHCT	KS54AHCT		Unit
				Typ	T _a = -40°C to +85°C	T _a = -55°C to +125°C		
Minimum High-Level Input Voltage	V _{IH}			2.0	2.0	2.0	V	
Maximum Low-Level Input Voltage	V _{IL}			0.8	0.8	0.8	V	
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL} I _O = -20μA I _O = -6mA	V _{CC} 4.2	V _{CC} - 0.1 3.98	V _{CC} - 0.1 3.84	V _{CC} - 0.1 3.7	V	
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL} I _O = 20μA I _O = 12mA I _O = 24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V	
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	±1.0	μA	
Maximum 3-State Leakage Current	I _{OZ}	Output Enable =V _{IH} V _{OUT} =V _{CC} or GND		±0.5	±5.0	±10.0	μA	
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0	μA	
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I =2.4V other Inputs: at V _{CC} or GND I _{OUT} =0μA		2.7	2.9	3.0	mA	



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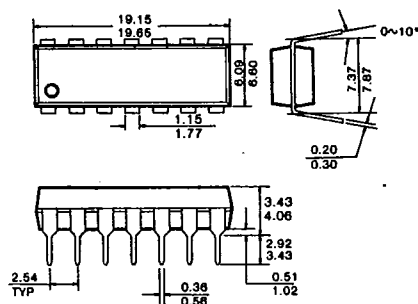
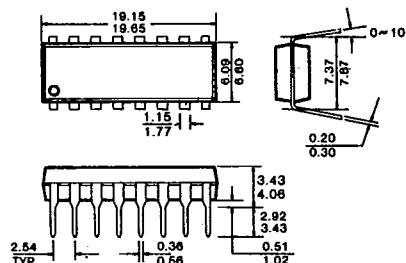
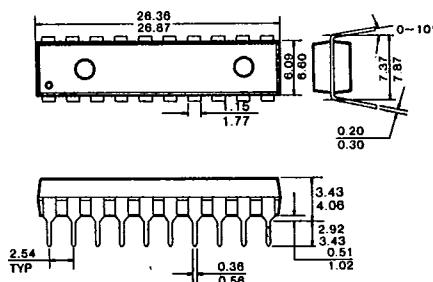
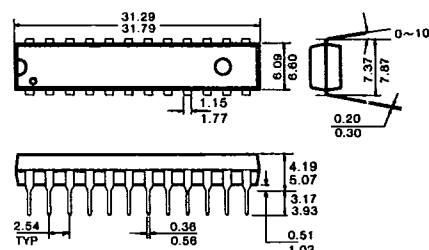
KS54AHCT 573
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AC ELECTRICAL CHARACTERISTICS (Input $t_r, t_f \leq 2$ ns), AHCT573

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay, D to Q	t_{PLH}	$C_L = 50\text{pF}$	9		14		17	ns
		$C_L = 150\text{pF}$	12		19		23	
	t_{PHL}	$C_L = 50\text{pF}$	9		14		17	
		$C_L = 150\text{pF}$	12		19		23	
Propagation Delay, C to Q	t_{PLH}	$C = 50\text{pF}$	12		20		24	ns
		$C_L = 150\text{pF}$	15		25		30	
	t_{PHL}	$C_L = 50\text{pF}$	12		20		24	
		$C_L = 150\text{pF}$	15		25		30	
Output Enable Time OC to any Q	t_{PZH}	$C_L = 50\text{pF}$	11		18		22	ns
		$R_L = 1\text{k}\Omega$ $C_L = 150\text{pF}$	14		23		28	
	t_{PZL}	$C_L = 50\text{pF}$	11		18		22	
		$C_L = 150\text{pF}$	14		23		28	
Output Disable Time OC to any Q	t_{PHZ}	$R_L = 1\text{k}\Omega$	13		19		22	ns
	t_{PLZ}	$C_L = 50\text{pF}$	13		19		22	
Pulse Width, C High	t_w		9	15*		18		ns
Setup Time, D before C↓	t_{su}		6	10		12		ns
Hold Time, D after C↓	t_h		4	7		9		ns
Input Capacitance	C_{IN}		5					pF
Output Capacitance	C_{OUT}	Output Disabled	10					pF
Power Dissipation Capacitance* (per stage)	C_{PD}	$\overline{OC} = V_{CC}$	5					pF
		$\overline{OC} = \text{GND}$	30					

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.



PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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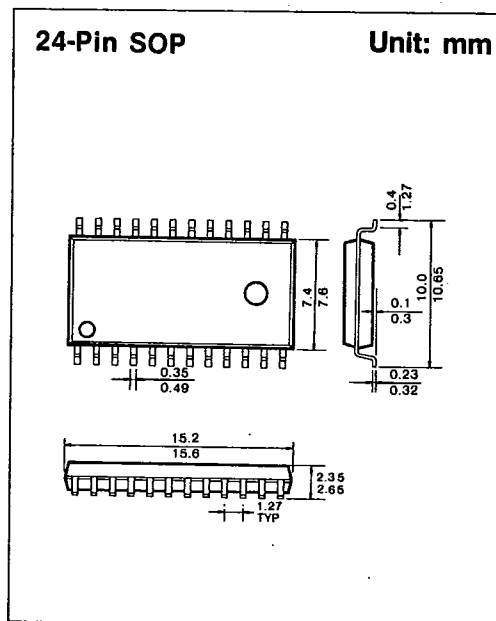
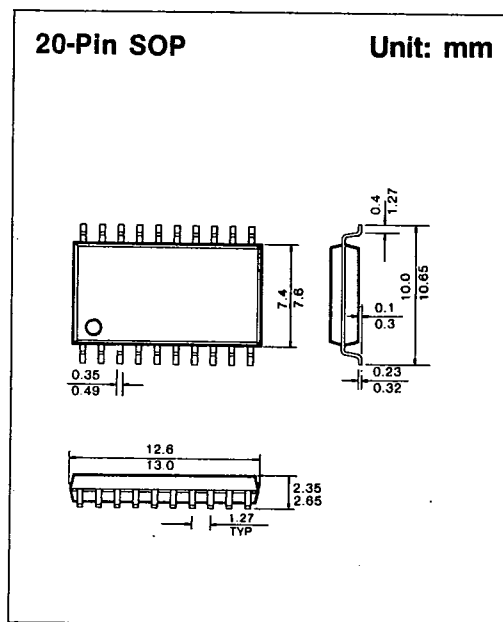
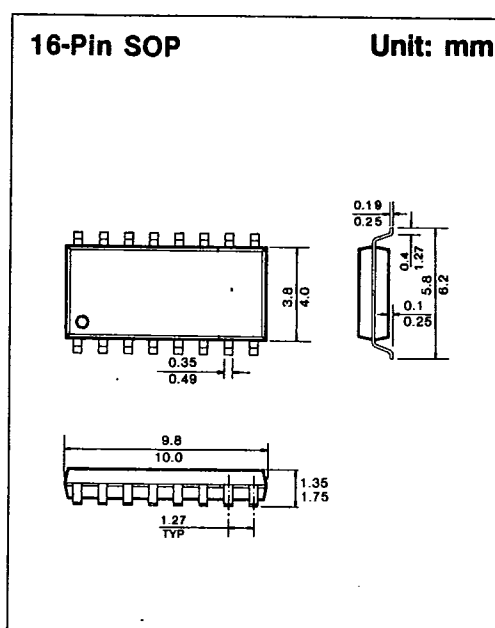
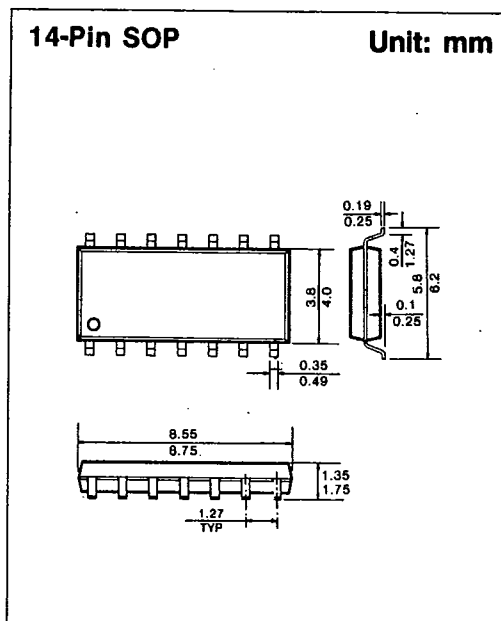
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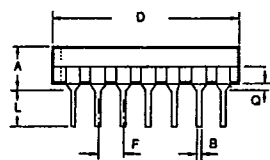
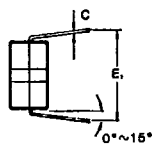
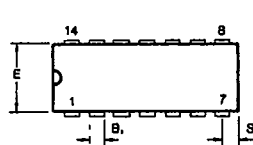
PACKAGE DIMENSIONS

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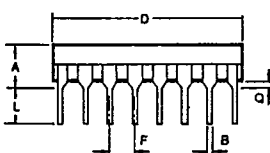
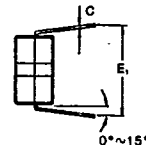
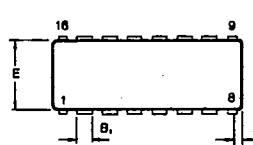


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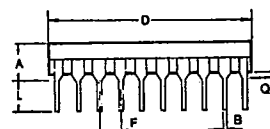
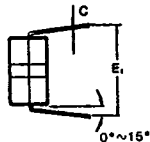
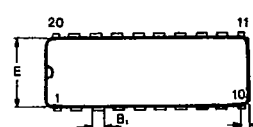
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2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

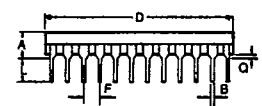
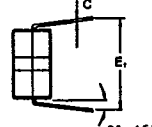
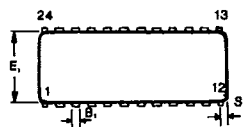
Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93

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